

2SA673A (PNP) and 2SC1213A (NPN) are silicon epitaxial transistors designed for medium power amplifiers and switching applications. 2SA673A (PNP) is complementary to 2SC1213A (NPN).

T0-92



ECB

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	50V
Collector-Emitter Voltage	VCEO	50V
Emitter-Base Voltage	VEBO	4V
Collector Current	IC	500mA
Total Power Dissipation	Ptot	400mW
Operating Junction & Storage Temperature	Tj, Tstg	-55 to +150°C

ELECTRICAL CHARACTERISTICS (TA=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector Cutoff Current	ICBO		500	nA	VCB=20V IE=0
D.C. Current Gain	HFE	60	320		IC=10mA VCE=3V
Collector-Emitter Saturation Voltage	VCE(sat)		0.4	V	IC=100mA IB=10mA*
Base-Emitter Saturation Voltage	VBE(sat)		1	V	IC=100mA IB=10mA*
Collector-Base Breakdown Voltage	BVCBO	50		V	IC=100µA IE=0
Collector-Emitter Breakdown Voltage	LVCEO	50		V	IC=10mA IB=0
Emitter-Base Breakdown Voltage	BVEBO	4		V	IE=100µA IC=0
Current Gain-Bandwidth Product	fT	120 TYP.		MHz	IC=10mA VCE=10V
Output Capacitance	Cob		7TYP.	pF	VCB=10V f=1MHz



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